Maximum Ratings (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	VALUE
Collector-Base Voltage	V_{CBO}	V	40
Collector-Emitter Voltage	V_{CEO}		25
Emitter-Base Voltage	V_{EBO}		5.0
Collector Current	I_C	A	1.5
Collector Power Dissipation	P_C	mW	300
Storage temperature	T_{stg}	°C	-55 ~+150
Junction temperature	T_j	°C	-55 ~+150
Typical Thermal Resistance	$R_{\theta J-A}$	°C /W	417

Electrical Characteristics (Ta=25°C Unless otherwise noted)

PARAMETER	SYMBOL	UNIT	Condition	Min	Max
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	V	I_C=100μA, I_E=0	40	—
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$		I_C=100μA, I_B=0	25	—
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$		I_E=100μA, I_C=0	5.0	—
Collector-Base cut-off current	I_{CBO}	μA	V_{CB}=40V, I_E=0	—	0.1
Collector-Emitter cut-off current	I_{CEO}		V_{CE}=20V, I_B=0	—	0.1
Emitter-Base cut-off current	I_{EBO}		V_{EB}=5.0V, I_C=0	—	0.1
DC Current Gain	$h_{FE(1)}$	—	I_C=100mA, V_{CE}=1.0V	120	350
	$h_{FE(2)}$		I_C=800mA, V_{CE}=1.0V	40	—
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	V	I_C=800mA, I_B=80mA	—	0.5
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	V	I_C=800mA, I_B=80mA	—	1.2